

isc Silicon PNP Power Transistor

2SA1486

DESCRIPTION

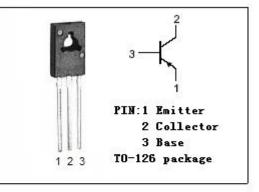
- Collector-Emitter Breakdown Voltage-: V_{(BR)CEO}= -80V(Min)
- With TO-126 package
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

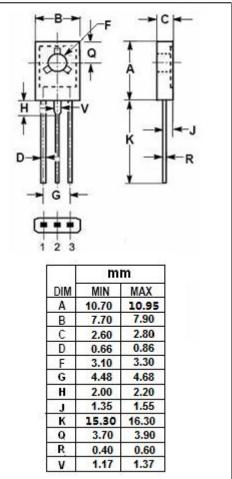
APPLICATIONS

• Designed for low frequency power amplifiers applications.

$\begin{array}{ c c c c } \label{eq:symbol} \mathbf{SYMBOL} & \mathbf{PARAMETER} & \mathbf{VALUE} & \mathbf{UNIT} \\ \hline \\ $							
$\frac{V_{CEO}}{V_{CEO}} = \frac{Collector-Emitter Voltage}{Collector-Emitter Voltage} = \frac{-600}{V}$ $\frac{V_{EBO}}{V_{EBO}} = \frac{Emitter-Base Voltage}{Collector Current-Continuous} = \frac{-7}{-1}$ $\frac{V}{I_C} = \frac{Collector Current-Peak}{Collector Current-Peak} = \frac{-2}{-2}$ $\frac{Collector Power Dissipation}{@Ta=25^{\circ}C} = \frac{1}{10}$ W	SYMBOL	PARAMETER	VALUE	UNIT			
$\frac{V_{EBO}}{I_{C}} = \frac{Emitter-Base Voltage}{Emitter-Base Voltage} -7 \qquad V$ $\frac{I_{C}}{I_{C}} = \frac{Collector Current-Continuous}{Collector Current-Peak} -1 \qquad A$ $\frac{I_{CM}}{P_{C}} = \frac{Collector Current-Peak}{Q^{T}a=25^{\circ}C} \qquad 1 \qquad W$ $\frac{Collector Power Dissipation}{Q^{T}a=25^{\circ}C} \qquad 10$	V _{CBO}	Collector-Base Voltage	-600	v			
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	V _{CEO}	Collector-Emitter Voltage	-600	V			
$\begin{array}{c c} I_{CM} & Collector Current-Peak & -2 & A \\ \\ \hline P_{C} & \hline & \\ \hline & \\ \hline & \\ Collector Power Dissipation \\ \hline & \\ \hline \hline \hline \\ \hline \hline \hline \hline \\ \hline \hline \hline \hline \\ \hline \hline$	V _{EBO}	Emitter-Base Voltage	-7	V			
$P_{c} = \begin{bmatrix} Collector Power Dissipation \\ @Ta=25^{\circ}C \\ \hline Collector Power Dissipation \\ @T_{c}=25^{\circ}C \\ \hline \end{bmatrix} \begin{bmatrix} 0 \\ W \\ 10 \\ 0 \end{bmatrix}$	lc	Collector Current-Continuous	-1	A			
$P_{C} = \begin{bmatrix} @Ta=25^{\circ}C & 1 \\ Collector Power Dissipation \\ @T_{C}=25^{\circ}C & 10 \end{bmatrix} W$	I _{CM}	Collector Current-Peak	-2	А			
Collector Power Dissipation 10			1	W			
T _J Junction Temperature 150 °C	Pc		10				
	TJ	Junction Temperature	150	°C			
T _{stg} Storage Temperature -55~150 °C	T _{stg}	Storage Temperature	-55~150	°C			

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)







isc Silicon PNP Power Transistor

2SA1486

ELECTRICAL CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -1mA; R _{BE} =∞	-600			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -0.3Α; I _B = -0.06Α			-1.0	V
$V_{\text{BE}(\text{sat})}$	Base-Emitter Saturation Voltage	I _C = -0.3Α; I _B = -0.06Α			-1.2	V
Ісво	Collector Cutoff Current	V _{CB} = -600V; I _E = 0			-10	μA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-10	μA
h _{FE -1}	DC Current Gain	I _C = -0.1A; V _{CE} = -5V	30		120	
h _{FE} -2	DC Current Gain	I _C = -0.5A; V _{CE} = -5V	5			

• h_{FE -1}Classifications

М	L	к
30-60	40-80	60-120

Notice:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.